

# MHQ2483

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CASE 632-02, STYLE 1  
TO-116

QUAD  
AMPLIFIER TRANSISTOR

NPN SILICON

## MAXIMUM RATINGS

Rating	Symbol	Value		Unit
		Each Transistor	Total Device	
Collector-Emitter Voltage	V <sub>CEO</sub>	40		Vdc
Collector-Base Voltage	V <sub>CBO</sub>	60		Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	6.0		Vdc
Collector Current — Continuous	I <sub>C</sub>	50		mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	0.6 3.42	1.8 10.3	Watts mW/C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.2 6.85	4.2 24	Watts mW/C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>Stg</sub>	-65 to +200		°C

Refer to 2N2919 for graphs.

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	40	—	—	Vdc
Collector-Base Breakdown Voltage (I <sub>C</sub> = 10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	60	—	—	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6.0	—	—	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 45 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	—	—	20	nAdc
Emitter Cutoff Current (V <sub>BE</sub> = 3.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	—	—	20	nAdc

### ON CHARACTERISTICS

DC Current Gain (I <sub>C</sub> = 0.1 mA, V <sub>CE</sub> = 5.0 Vdc)	MHQ2483 MHQ2484	$\text{h}_{FE}$	100	—	—	—
(I <sub>C</sub> = 1.0 mA, V <sub>CE</sub> = 5.0 Vdc)	MHQ2483 MHQ2484		200	—	—	—
(I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 Vdc)	MHQ2483 MHQ2484		150	—	—	—
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 1.0 mA, I <sub>B</sub> = 0.1 mA) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1.0 mA)	V <sub>CE(sat)</sub>	300	—	—	—	—
—	—	150	—	—	—	—
—	—	300	—	—	—	—
Base-Emitter On Voltage (I <sub>C</sub> = 100 μA, V <sub>CE</sub> = 5.0 Vdc) (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 Vdc)	V <sub>BE(on)</sub>	—	0.13	0.35	Vdc	—
—	—	—	0.15	0.5	—	—
—	—	—	0.58	0.7	Vdc	—
—	—	—	0.70	0.8	—	—

### SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product (I <sub>C</sub> = 500 μA, V <sub>CE</sub> = 5.0 Vdc, f = 20 MHz)	f <sub>T</sub>	50	100	—	MHz
Input Capacitance (V <sub>BE</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 100 kHz)	C <sub>ibo</sub>	—	4.0	8.0	pF
Collector-Base Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 100 kHz)	C <sub>cb</sub>	—	1.8	6.0	pF
Noise Figure (I <sub>C</sub> = 10 μA, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 10 kohms, f = 10 Hz to 15.7 kHz, BW = 10 kHz)	NF	—	3.0	—	dB
		—	2.0	—	